

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type ( $\pi$ -MOSIII)

## 2SK2884

Chopper Regulator, DC-DC Converter Applications

Unit: mm

- Low drain-source ON resistance :  $R_{DS(ON)} = 1.9 \Omega$  (typ.)
- High forward transfer admittance :  $|Y_{fs}| = 3.8 S$  (typ.)
- Low leakage current :  $I_{DSS} = 100 \mu A$  (max) ( $V_{DS} = 640 V$ )
- Enhancement mode :  $V_{th} = 2.0 \sim 4.0 V$  ( $V_{DS} = 10 V$ ,  $I_D = 1 mA$ )

### Absolute Maximum Ratings ( $T_a = 25^\circ C$ )

| Characteristics                              |                | Symbol    | Rating         | Unit       |
|--|----------------|-----------|----------------|------------|
| Drain-source voltage                         |                | $V_{DSS}$ | 800            | V          |
| Drain-gate voltage ( $R_{GS} = 20 k\Omega$ ) |                | $V_{DGR}$ | 800            | V          |
| Gate-source voltage                          |                | $V_{GSS}$ | $\pm 30$       | V          |
| Drain current                                | DC (Note 1)    | $I_D$     | 5              | A          |
|  | Pulse (Note 1) | $I_{DP}$  | 15             | A          |
| Drain power dissipation                      |                | $P_D$     | 100            | W          |
| Single pulse avalanche energy (Note 2)       |                | $E_{AS}$  | 370            | mJ         |
| Avalanche current                            |                | $I_{AR}$  | 5              | A          |
| Repetitive avalanche energy (Note 3)         |                | $E_{AR}$  | 10             | mJ         |
| Channel temperature                          |                | $T_{ch}$  | 150            | $^\circ C$ |
| Storage temperature range                    |                | $T_{stg}$ | $-55 \sim 150$ | $^\circ C$ |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

### Thermal Characteristics

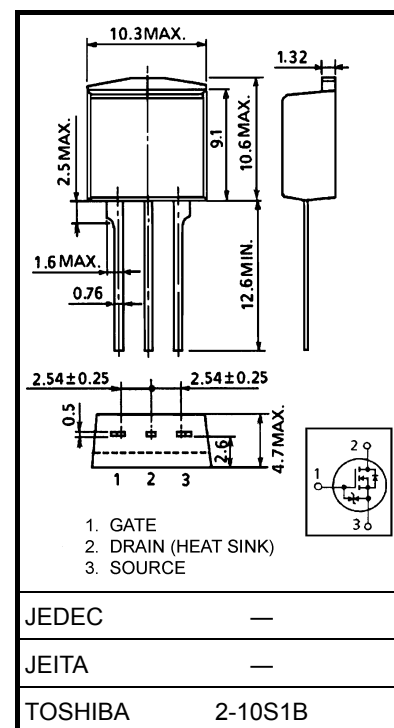
| Characteristics                        | Symbol         | Max  | Unit           |
|--|----------------|------|----------------|
| Thermal resistance, channel to case    | $R_{th(ch-c)}$ | 1.25 | $^\circ C / W$ |
| Thermal resistance, channel to ambient | $R_{th(ch-a)}$ | 83.3 | $^\circ C / W$ |

Note 1: Ensure that the channel temperature does not exceed  $150^\circ C$ .

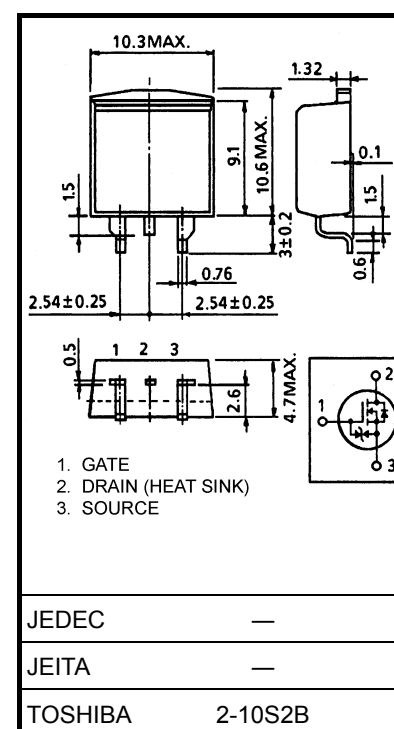
Note 2:  $V_{DD} = 90 V$ ,  $T_{ch} = 25^\circ C$  (initial),  $L = 27 mH$ ,  $R_G = 25 \Omega$ ,  $I_{AR} = 5 A$

Note 3: Repetitive rating: pulse width limited by maximum channel temperature.

This transistor is an electrostatic-sensitive device.  
Please handle with caution.

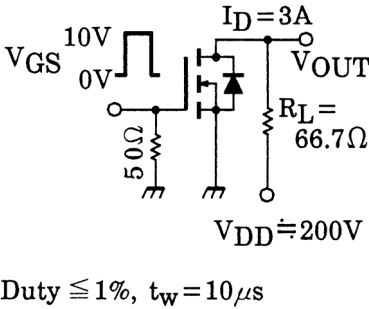


Weight: 1.5 g (typ.)



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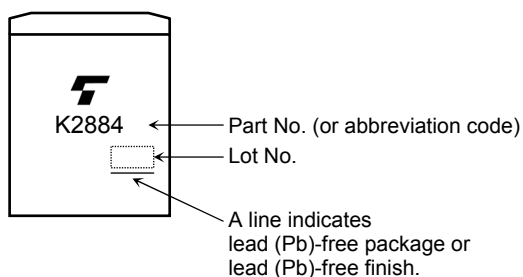
## Electrical Characteristics (Ta = 25°C)

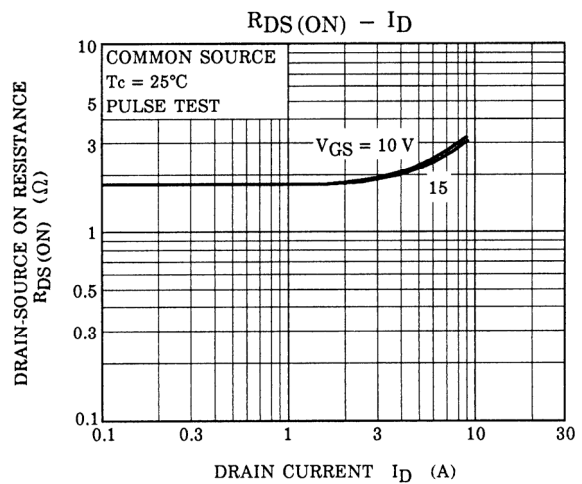
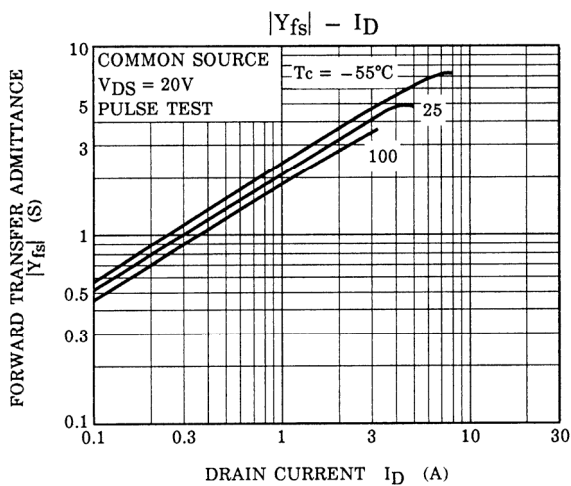
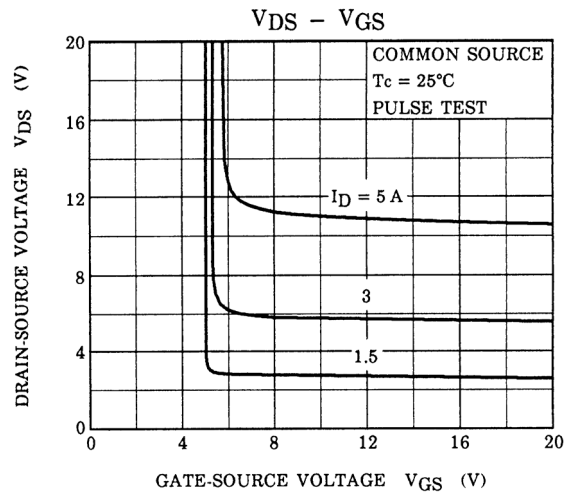
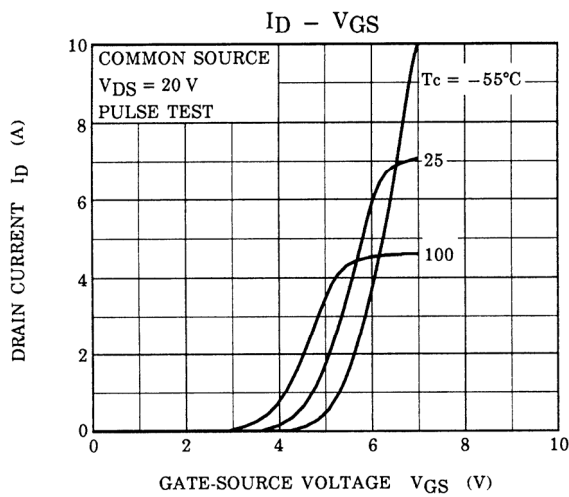
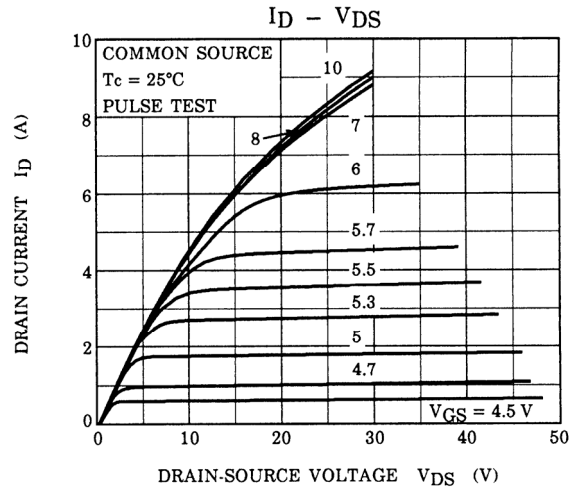
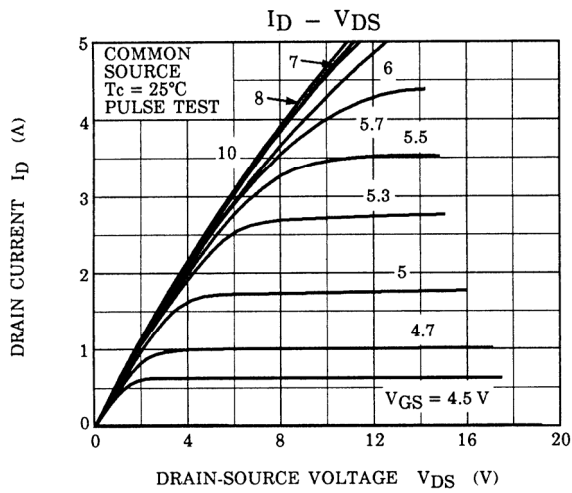
| Characteristics                                 |               | Symbol         | Test Condition  | Min      | Typ. | Max      | Unit          |
|---|---------------|----------------|---|----------|------|----------|---------------|
| Gate leakage current                            |               | $I_{GSS}$      | $V_{GS} = \pm 30 \text{ V}$ , $V_{DS} = 0 \text{ V}$  | —        | —    | $\pm 10$ | $\mu\text{A}$ |
| Gate-source breakdown voltage                   |               | $V_{(BR) GSS}$ | $I_G = \pm 10 \mu\text{A}$ , $V_{DS} = 0 \text{ V}$   | $\pm 30$ | —    | —        | V             |
| Drain cut-off current                           |               | $I_{DSS}$      | $V_{DS} = 640 \text{ V}$ , $V_{GS} = 0 \text{ V}$   | —        | —    | 100      | $\mu\text{A}$ |
| Drain-source breakdown voltage                  |               | $V_{(BR) DSS}$ | $I_D = 10 \text{ mA}$ , $V_{GS} = 0 \text{ V}$  | 800      | —    | —        | V             |
| Gate threshold voltage                          |               | $V_{th}$       | $V_{DS} = 10 \text{ V}$ , $I_D = 1 \text{ mA}$  | 2.0      | —    | 4.0      | V             |
| Drain-source ON resistance                      |               | $R_{DS (ON)}$  | $V_{GS} = 10 \text{ V}$ , $I_D = 3 \text{ A}$   | —        | 1.9  | 2.2      | $\Omega$      |
| Forward transfer admittance                     |               | $ Y_{fs} $     | $V_{DS} = 15 \text{ V}$ , $I_D = 3 \text{ A}$   | 1.0      | 3.8  | —        | S             |
| Input capacitance                               |               | $C_{iss}$      | $V_{DS} = 25 \text{ V}$ , $V_{GS} = 0 \text{ V}$ , $f = 1 \text{ MHz}$  | —        | 1080 | —        | pF            |
| Reverse transfer capacitance                    |               | $C_{rss}$      |   | —        | 16   | —        |               |
| Output capacitance                              |               | $C_{oss}$      |   | —        | 105  | —        |               |
| Switching time                                  | Rise time     | $t_r$          |  <p><math>I_D = 3 \text{ A}</math><br/><math>R_L = 66.7 \Omega</math><br/><math>V_{DD} \approx 200 \text{ V}</math><br/><math>\text{Duty} \leq 1\%</math>, <math>t_w = 10 \mu\text{s}</math></p> | —        | 40   | —        | ns            |
|   | Turn-on time  | $t_{on}$       |   | —        | 80   | —        |               |
|   | Fall time     | $t_f$          |   | —        | 40   | —        |               |
|   | Turn-off time | $t_{off}$      |   | —        | 140  | —        |               |
| Total gate charge (gate-source plus gate-drain) |               | $Q_g$          | $V_{DD} \approx 400 \text{ V}$ , $V_{GS} = 10 \text{ V}$ , $I_D = 5 \text{ A}$  | —        | 34   | —        | nC            |
| Gate-source charge                              |               | $Q_{gs}$       |   | —        | 16   | —        |               |
| Gate-drain ("miller") Charge                    |               | $Q_{gd}$       |   | —        | 18   | —        |               |

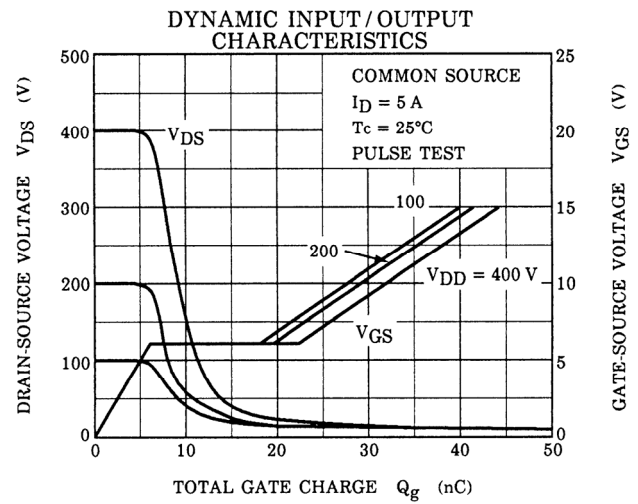
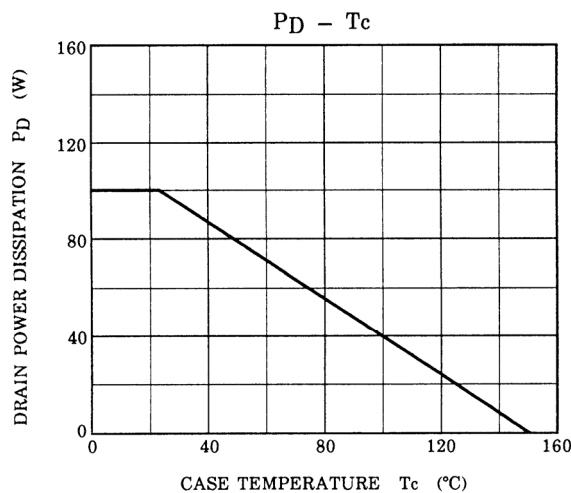
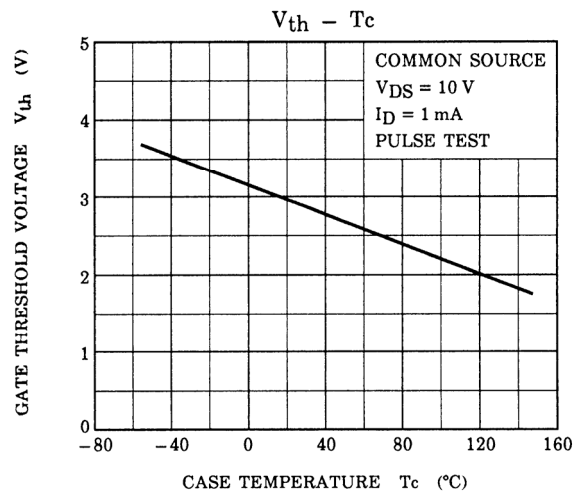
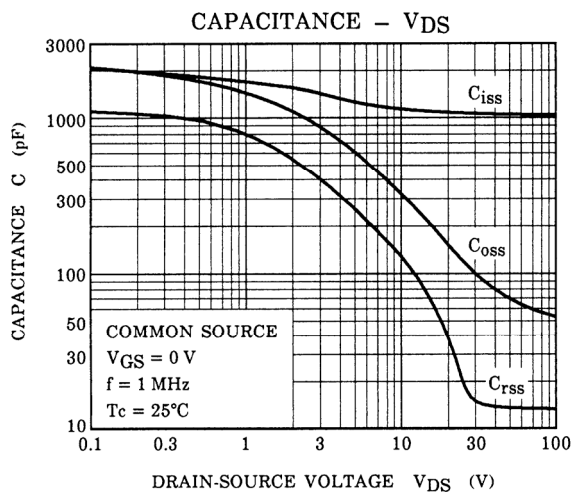
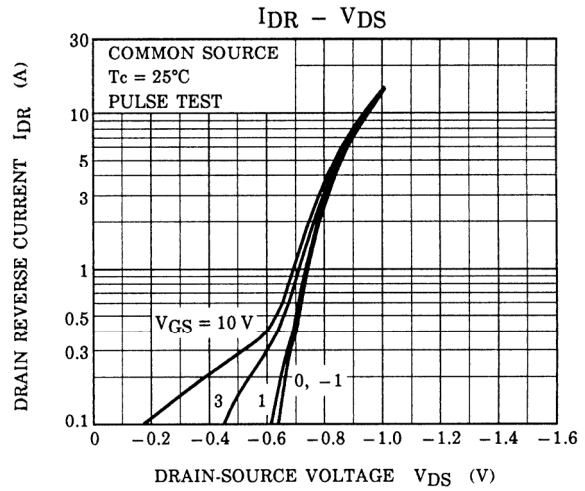
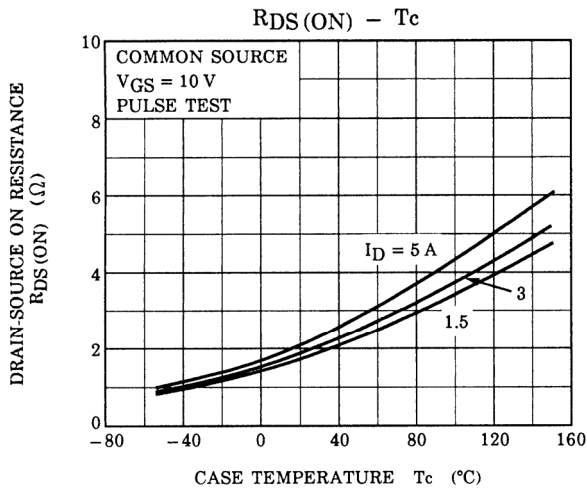
## Source-Drain Ratings and Characteristics (Ta = 25°C)

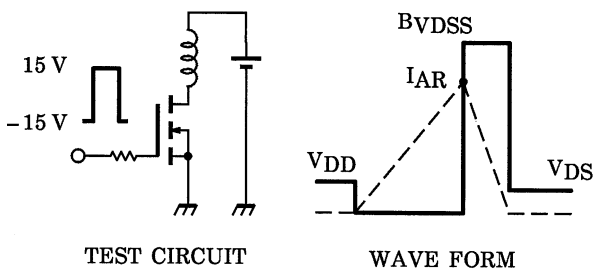
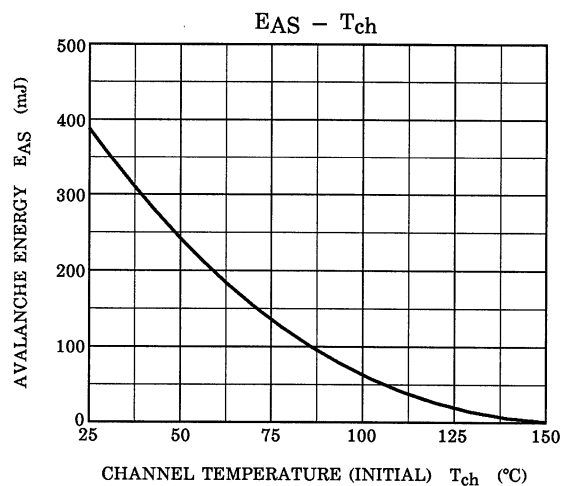
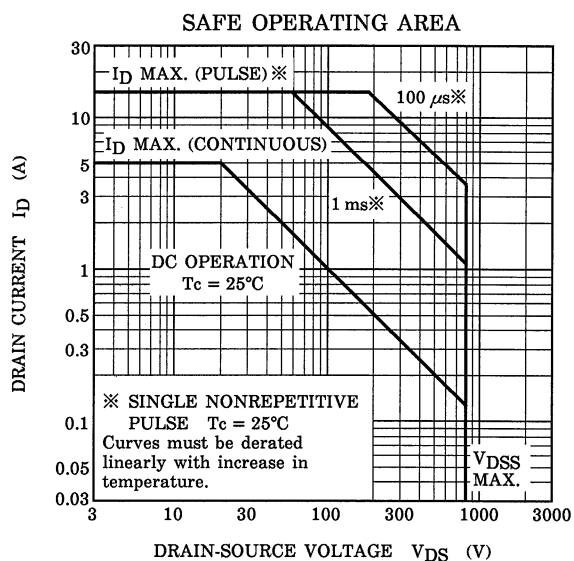
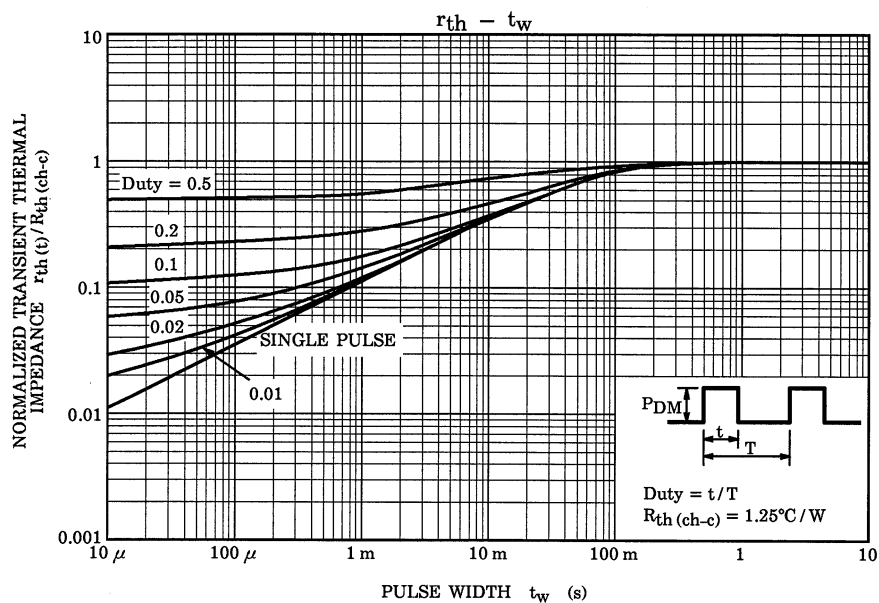
| Characteristics                           | Symbol    | Test Condition                                  | Min | Typ. | Max  | Unit          |
|---|-----------|---|-----|------|------|---------------|
| Continuous drain reverse current (Note 1) | $I_{DR}$  | —   | —   | —    | 5    | A             |
| Pulse drain reverse current (Note 1)      | $I_{DRP}$ | —   | —   | —    | 15   | A             |
| Forward voltage (diode)                   | $V_{DSF}$ | $I_{DR} = 5 \text{ A}$ , $V_{GS} = 0 \text{ V}$ | —   | —    | -1.9 | V             |
| Reverse recovery time                     | $t_{rr}$  | $I_{DR} = 5 \text{ A}$ , $V_{GS} = 0 \text{ V}$ | —   | 1000 | —    | ns            |
| Reverse recovery charge                   | $Q_{rr}$  | $dI_{DR} / dt = 100 \text{ A} / \mu\text{s}$    | —   | 7.5  | —    | $\mu\text{C}$ |

## Marking









$$R_G = 25 \, \Omega$$

$$V_{DD} = 90 \, \text{V}, L = 27 \, \text{mH}$$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left( \frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

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20070701-EN

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